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Case Docket No. 980221

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PATENTS ONLY

To the Assistant Commissioner for Patents.
Please record the attached original documents or copy thereof.

1. Name of conveying party:

Tadashi OSHIMA

Additional name(s) of conveying party(ies) attached? NO

2. Name and address of receiving party(ies):

Name: FUJITSU LIMITED

Street Address:

1-1, Kamikodanaka 4-chome, Nakahara-ku,
Kawasaki-shi, Kanagawa 211-8588, Japan

Additional name(s) & address(es) attached? NO

3. Nature of conveyance: **Assignment**

Execution Date: February 13, 1998

4. Title:

**METHOD OF ETCHING SILICON NITRIDE LAYER AND
METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE**

5. Application number(s) or patent number(s): 09/030,018

If this document is being filed together with a new application, the execution date of the application is:

A. Patent Application No.(s) B. Patent No.(s)

Additional numbers attached? NO

06/01/1998 10:00:00 AM 09/030,018

U.S. PATENT

06/01/98

PATENT

REEL: 9199 FRAME: 0296

6. Name and address of party to whom correspondence concerning document should be mailed:

Name: Armstrong, Westerman, Hattori,
McLeland & Naughton
Suite 1000
1725 K Street, N.W.
Washington, D.C. 20006

7. Total number of applications and patents involved: 1

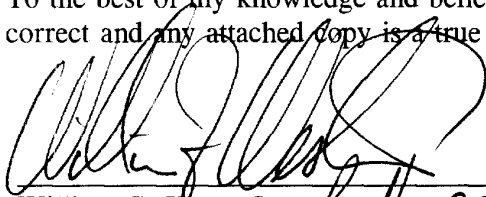
8. Total fee (37 CFR 3.41). \$ **40.00**

XX Check enclosed

9. Deposit Account No.: **01-2340**

10. Statement and signature.

To the best of my knowledge and belief, the foregoing information is true and correct and ~~any attached copy is a~~ true copy of the original document.


William G. Kratz, Jr.
Reg. No.: 22,631

Date May 18, 1998

Ex. No. 29,988

Total number of pages including cover sheet: 3

WGK/tmb

Armstrong, Westerman, Hattori, McLeland & Naughton

Docket No. 980221

U.S. ASSIGNMENT

IN CONSIDERATION of the sum of One Dollar (\$1.00), and of other good and valuable consideration paid to the undersigned inventor(s) (hereinafter ASSIGNOR) by

(Insert ASSIGNEE's
Name(s) Address(es))

FUJITSU LIMITED, 1-1, Kamikodanaka 4-chome, Nakahara-ku,
Kawasaki-shi, Kanagawa 211-8588 Japan
(hereinafter ASSIGNEE), the receipt of which is hereby acknowledged, the undersigned ASSIGNOR hereby sells, assigns and transfers to ASSIGNEE the entire and exclusive right, title and interest to the invention entitled

(Title of Invention)

METHOD OF ETCHING SILICON NITRIDE LAYER AND
METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE
for which application for Letters Patent of the United States was executed on even date herewith unless otherwise indicated below:

(*If the assignment is
being filed after the filing
of the application, this
section must be
completed)

*filed on February 25, 1998, Serial No. 09/030,018
(Armstrong, Westerman, Hattori, McLeland & Naughton is hereby authorized to insert the series code, serial number and/or filing date hereon, when known)

and all Letters Patent of the United States to be obtained therefor on said application or any continuation, divisional, substitute, reissue or reexamination thereof for the full term or terms for which the same may be granted.

The ASSIGNOR agrees to execute all papers necessary in connection with the application and any continuation, divisional, reissue or reexamination applications thereof and also to execute separate assignments in connection with such applications as the ASSIGNEE may deem necessary or expedient.

The ASSIGNOR agrees to execute all papers necessary in connection with any interference, litigation, or other legal proceeding which may be declared concerning this application or any continuation, divisional, reissue or reexamination thereof or Letters Patent or reissue patent issued thereon and to cooperate with the ASSIGNEE in every way possible in obtaining and producing evidence and proceeding with such interference, litigation, or other legal proceeding.

IN WITNESS WHEREOF, the undersigned inventor(s) has (have) affixed his/her/their signature(s).

(Signatures)

<u>Tadashi Oshima</u> (SIGNATURE)	<u>Tadashi OSHIMA</u> (TYPE NAME)	<u>Feb. 13, 1998</u> (DATE)
_____ (SIGNATURE)	_____ (TYPE NAME)	_____ (DATE)
_____ (SIGNATURE)	_____ (TYPE NAME)	_____ (DATE)
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_____ (SIGNATURE)	_____ (TYPE NAME)	_____ (DATE)
_____ (SIGNATURE)	_____ (TYPE NAME)	_____ (DATE)
_____ (SIGNATURE)	_____ (TYPE NAME)	_____ (DATE)

NO LEGALIZATION REQUIRED